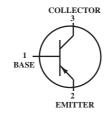


# **General Purpose Transistor PNP Silicon**



**Pb** Lead(Pb)-Free





## **Maximum Ratings**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	-40	V
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current-Continuous	Ic	-200	mA

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board <sup>(1)</sup> TA=25°C	P <sub>D</sub>	200	mW
Derate above 25°C		1.6	mW/°C
Thermal Resistance, Junction to Ambient	R <sub>OJA</sub>	600	°C/W
Total Device Dissipation Alumina Substrate, <sup>(2)</sup> TA=25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\Theta JA}$	400	°C/W
Junction Temperature	TJ	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

### **Device Marking**

MMBT3906T = 2A

### Electrical Characteristics (TA=25°C Unless Otherwise noted)

Characteristics	Symbol	Min	Max	Unit
Off Characteristics				
Collector-Emitter Breakdown Voltage <sup>(3)</sup> (I <sub>C</sub> =-1.0mAdc.IB=0)	V <sub>(BR)</sub> CEO	-40	-	٧
Collector-Base Breakdown Voltage (IC=-10 µAdc, IE=0)	V <sub>(BR)</sub> CBO	-40	-	V
Emitter-Base Breakdown Voltage (IE=-10 µAdc, IC=0)	V(BR)EBO	-5.0	-	V
Base Cutoff Current (VCE=-30 Vdc, VEB =-3.0 Vdc)	I <sub>BL</sub>	-	-50	nA
Collector Cutoff Current (VCE=-30Vdc, VEB=-3.0Vdc)	I <sub>CEX</sub>	-	-50	nA

- 1. FR-4 Minimum Pad.
- 2. FR-4 1.0 x 1.0 Inch Pad.
- 3. Pulse Test : Pulse Width  $\leq$  300  $\mu$ S, Duty Cycle  $\leq$  2.0%.



## **Electrical Characteristics** (TA=25°C unless otherwise noted) (Countinued)

Characteristics Symbol William 172m2	Characteristics	Symbol	Min	Max	Unit
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#### On Characteristics (3)

DC Current Gain				
$(I_{C} = -0.1 \text{ mA}, V_{CE} = -1.0V)$		60	-	
$(I_{C}=-1.0 \text{ mA}, V_{CE}=-1.0 \text{ V})$		80	-	
$(I_C = -10 \text{ mA}, V_{CE} = -1.0V)$	H <sub>FE</sub>	100	300	_
$(I_C = -50 \text{ mA}, V_{CE} = -1.0V)$		60	-	
$(I_C = -100 \text{ mA}, V_{CE} = -1.0V)$		30	-	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = -10 mA, I <sub>B</sub> = -1.0mA) (I <sub>C</sub> = -50 mA, I <sub>B</sub> = -5.0mA)	V <sub>CE(sat)</sub>	-	-0.25 -0.4	V
Base-Emitter Saturation Voltage (I <sub>C</sub> = -10 mA , I <sub>B</sub> = -1.0 mA) (I <sub>C</sub> = -50 mA , I <sub>B</sub> = -5.0 mA)	VBE(sat)	-0.65 -	-0.85 -0.95	V

## **Small-signal Characteristics**

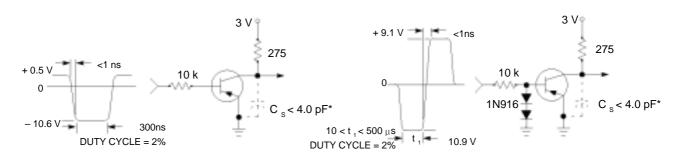
Current-Gain-Bandwidth Product (4) (I <sub>C</sub> = -10 mA , V <sub>C</sub> = -20 V , f=100MHz)	fT	250	-	MHz
Output Capacitance (V <sub>CB</sub> = -5.0 V, I <sub>E</sub> =0, f=1.0MHz)	C <sub>obo</sub>	-	4.5	pF
Input Capacitance (V <sub>EB</sub> = -0.5 V, I <sub>C</sub> =0, f=1.0MHz)	Cibo	-	10	рF
Input Impedance (VCE= -10V, IC=-1.0 mA, f=1.0 kHz)	h <sub>ie</sub>	2.0	12	kΩ
Voltage Feeback Radio (V <sub>CE</sub> = -10V, I <sub>C</sub> =-1.0 mA, f=1.0 kHz)	h <sub>re</sub>	0.1	10	x 10 <sup>-4</sup>
Small-Signal Current Gain (VCE= -10V, I <sub>C</sub> =-1.0 mA ,f=1.0 kHz)	h <sub>fe</sub>	100	400	-
Output Admittance (V <sub>CE</sub> = -10V, I <sub>C</sub> =-1.0 mA , f=1.0kHz)	h <sub>oe</sub>	3.0	60	μmhos
Noise Figure ( $V_{CE}$ = -5.0V, $I_{C}$ = -100 $\mu$ A , $R_{S}$ =1.0k $\Omega$ , f=1.0kHz)	NF	-	4.0	dB

## **Switching Characteristics**

Delay Time	(Vcc= -3.0 V, VBE= 0.5 V	td	-	35	
Rise Time	lc= -10 mA, lB1= -1.0 mA)	tr	-	35	ns
Storage Time	(Vcc= -3.0 V,	ts	-	225	ns
Fall Time	lc= -10 mA , lB1=lB2= -1.0 mA)	tf	-	75	113

<sup>3.</sup>Pulse Test:Pulse Width≦300 µS, Duty Cycle≦2.0%.





\*Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time **Equivalent Test Circuit** 

Figure 2. Storage and Fall Time **Equivalent Test Circuit** 

#### TYPICAL TRANSIENT CHARACTERISTICS

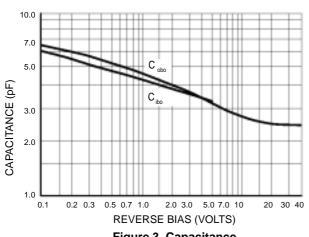


Figure 3. Capacitance

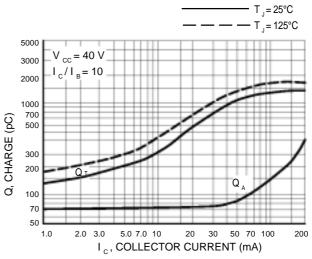


Figure 4. Charge Data

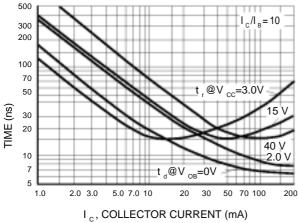


Figure 5. Turn-On Time

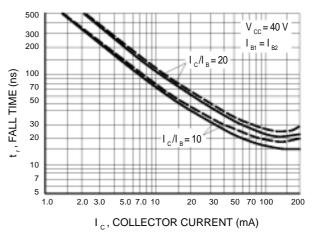


Figure 6. Fall Time



#### TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$ 

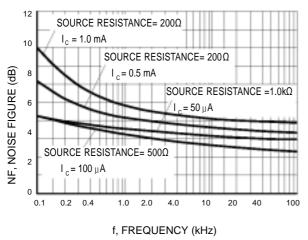


Figure 7. Noise Figure

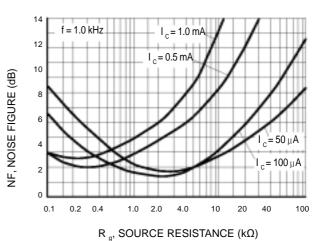


Figure 8. Noise Figure

#### h PARAMETERS

(V  $_{CE}$  = 10 Vdc, f = 1.0 kHz, T  $_{A}$  = 25°C)

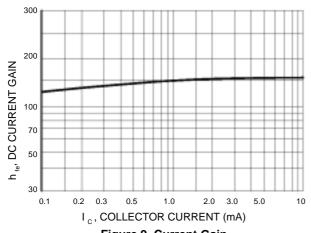


Figure 9. Current Gain



I<sub>c</sub>, COLLECTOR CURRENT (mA) **Figure 11. Input Impedance** 

1.0

2.0 3.0

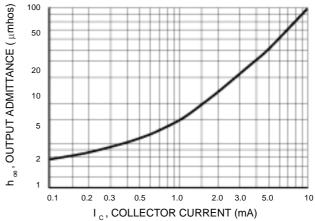


Figure 10. Output Admittance

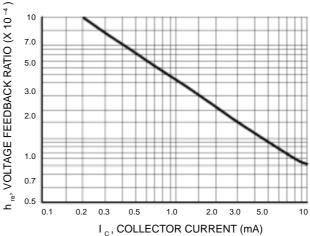


Figure 12. Voltage Feedback Ratio

5.0

2.0

1.0

0.5

0.2

h <sub>ie</sub>, INPUT IMPEDANCE (kΩ)



#### TYPICAL STATIC CHARACTERISTICS

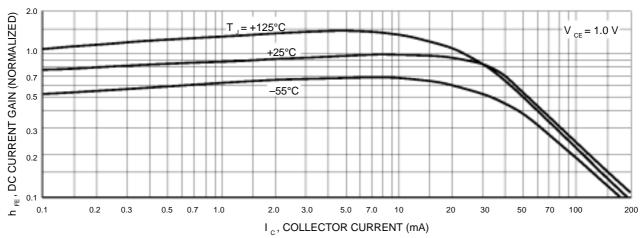


Figure 13. DC Current Gain

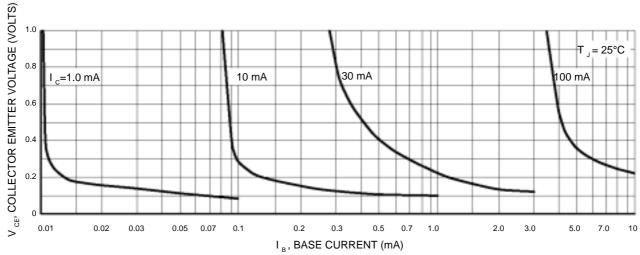
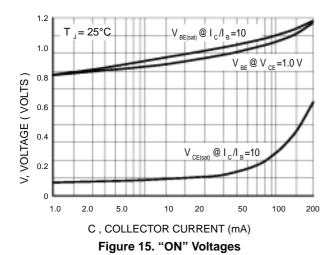


Figure 14. Collector Saturation Region



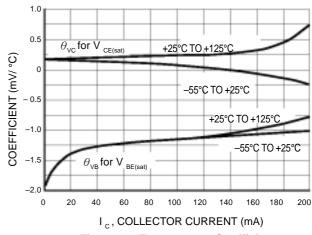


Figure 16. Temperature Coefficients



#### **SC-89 Package Outline Dimensions**

Unit:mm

